PD -50066A

International
IOR Rectifier

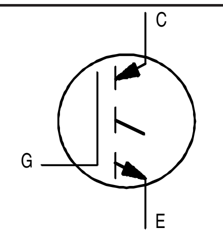
GA200SA60U

INSULATED GATE BIPOLAR TRANSISTOR

Ultra-Fast™ Speed IGBT

Features

- UltraFast: Optimized for minimum saturation voltage and operating frequencies up to 40 kHz in hard switching, > 200 kHz in resonant mode
- Very low conduction and switching losses
- Fully isolate package (2,500 Volt AC/RMS)
- Very low internal inductance (≤ 5 nH typ.)
- Industry standard outline



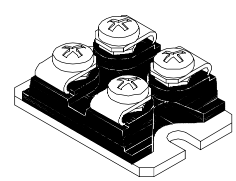
$V_{CES} = 600V$

$V_{CE(on)}$ typ. = 1.60V

@V_{GE} = 15V, I_C = 100A

Benefits

- Designed for increased operating efficiency in power conversion: UPS, SMPS, Welding, Induction heating
- Lower overall losses available at frequencies ≥ 20kHz
- Easy to assemble and parallel
- Direct mounting to heatsink
- Lower EMI, requires less snubbing
- Plug-in compatible with other SOT-227 packages



SOT-227

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Breakdown Voltage	600	V
I_C @ T_C = 25°C	Continuous Collector Current	200	A
I_C @ T_C = 100°C	Continuous Collector Current	100	
I_{CM}	Pulsed Collector Current	400	
I_{LM}	Clamped Inductive Load Current②	400	
V_{GE}	Gate-to-Emitter Voltage	± 20	V
E_{ARV}	Reverse Voltage Avalanche Energy ③	160	mJ
V_{ISOL}	RMS Isolation Voltage, Any Terminal to Case, t=1 min	2500	V
P_D @ T_C = 25°C	Maximum Power Dissipation	500	W
P_D @ T_C = 100°C	Maximum Power Dissipation	200	
T_J	Operating Junction	-55 to + 150	°C
T_{STG}	Storage Temperature Range	-55 to + 150	
	Mounting Torque, 6-32 or M3 Screw	12 lbf •in(1.3N•m)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	——	0.25	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.05	——	
Wt	Weight of Module	30	——	gm

4/24/2000

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	600	—	—	V	V_{GE} = 0V, I_C = 250µA
$V_{(BR)ECS}$	Emitter-to-Collector Breakdown Voltage ④	18	—	—	V	V_{GE} = 0V, I_C = 1.0A
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.38	—	V/°C	V_{GE} = 0V, I_C = 10 mA
$V_{CE(ON)}$	Collector-to-Emitter Saturation Voltage	—	1.60	1.9	V	I_C = 100A, V_{GE} = 15V
		—	1.92	—		I_C = 200A, See Fig.2, 5
		—	1.54	—		I_C = 100A , T_J = 150°C
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	6.0		V_{CE} = V_{GE}, I_C = 250µA
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-11	—	mV/°C	V_{CE} = V_{GE}, I_C = 2.0 mA
g_{fe}	Forward Transconductance ⑤	79		—	S	V_{CE} = 100V, I_C = 100A
I_{CES}	Zero Gate Voltage Collector Current	—	—	1.0	mA	V_{GE} = 0V, V_{CE} = 600V
		—	—	10		V_{GE} = 0V, V_{CE} = 600V, T_J = 150°C
I_{GES}	Gate-to-Emitter Leakage Current	—	—	±250	nA	V_{GE} = ±20V

Switching Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge (turn-on)	—	770	1200	nC	I_C = 100A
Q_{ge}	Gate - Emitter Charge (turn-on)	—	100	150		V_{CC} = 400V See Fig. 8
Q_{gc}	Gate - Collector Charge (turn-on)	—	260	380		V_{GE} = 15V
$t_{d(on)}$	Turn-On Delay Time	—	54	—	ns	
t_r	Rise Time	—	79	—		T_J = 25°C
$t_{d(off)}$	Turn-Off Delay Time	—	130	200		I_C = 100A, V_{CC} = 480V
t_f	Fall Time	—	300	450		V_{GE} = 15V, R_G = 2.0Ω
E_{on}	Turn-On Switching Loss	—	0.98	—	mJ	Energy losses include "tail"
E_{off}	Turn-Off Switching Loss	—	3.48	—		See Fig. 9, 10, 14
E_{ts}	Total Switching Loss	—	4.46	7.6		
$t_{d(on)}$	Turn-On Delay Time	—	56	—	ns	T_J = 150°C,
t_r	Rise Time	—	75	—		I_C = 100A, V_{CC} = 480V
$t_{d(off)}$	Turn-Off Delay Time	—	160	—		V_{GE} = 15V, R_G = 2.0Ω
t_f	Fall Time	—	460	—		Energy losses include "tail"
E_{ts}	Total Switching Loss	—	7.24	—	mJ	See Fig. 10, 11, 14
L_E	Internal Emitter Inductance	—	5.0	—	nH	Measured 5mm from package
C_{ies}	Input Capacitance	—	16500	—	pF	V_{GE} = 0V
C_{oes}	Output Capacitance	—	1000	—		V_{CC} = 30V See Fig. 7
C_{res}	Reverse Transfer Capacitance	—	200	—		f = 1.0MHz

Notes:

① Repetitive rating; V_{GE} = 20V, pulse width limited by max. junction temperature. (See fig. 13b)

② V_{CC} = 80%(V_{CES}), V_{GE} = 20V, L = 10µH, R_G = 2.0Ω, (See fig. 13a)

③ Repetitive rating; pulse width limited by maximum junction temperature.

④ Pulse width ≤ 80µs; duty factor ≤ 0.1%.

⑤ Pulse width 5.0µs, single shot.

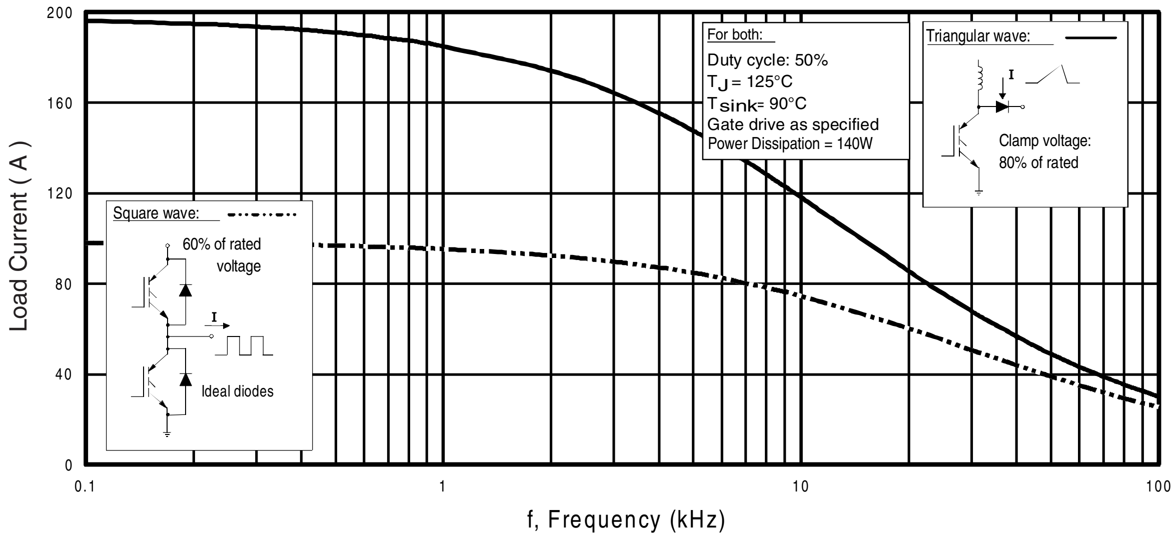


Fig. 1 - Typical Load Current vs. Frequency
(Load Current = I_{RMS} of fundamental)

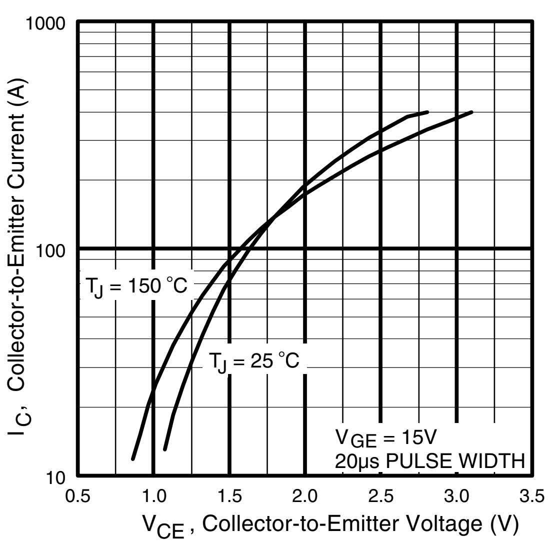


Fig. 2 - Typical Output Characteristics

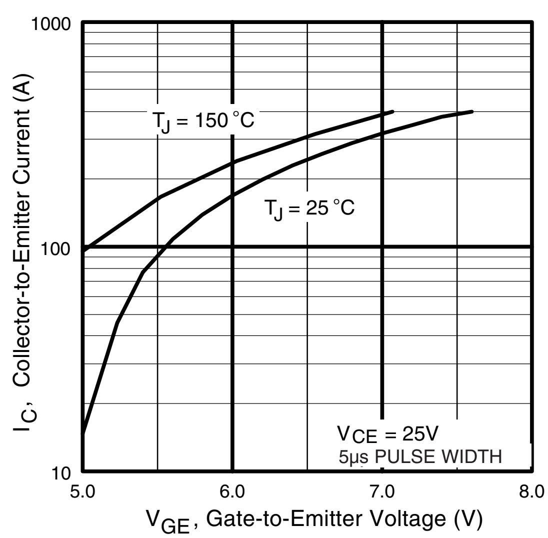


Fig. 3 - Typical Transfer Characteristics

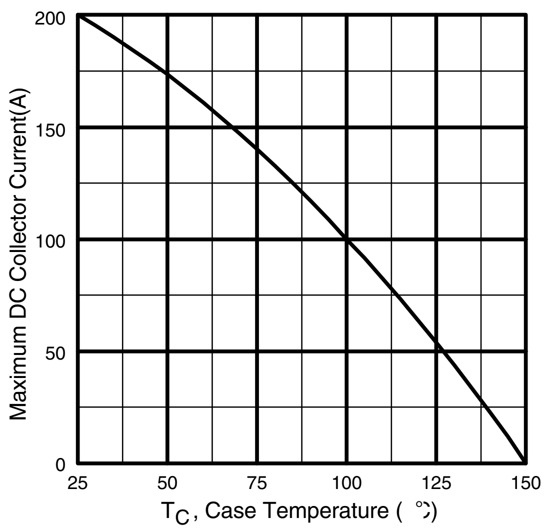


Fig. 4 - Maximum Collector Current vs. Case Temperature

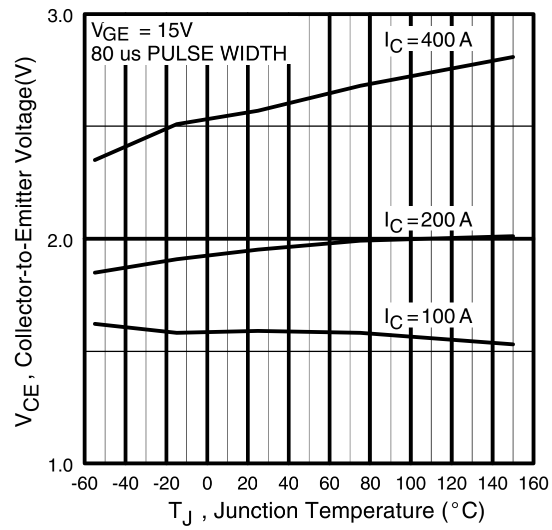


Fig. 5 - Typical Collector-to-Emitter Voltage vs. Junction Temperature

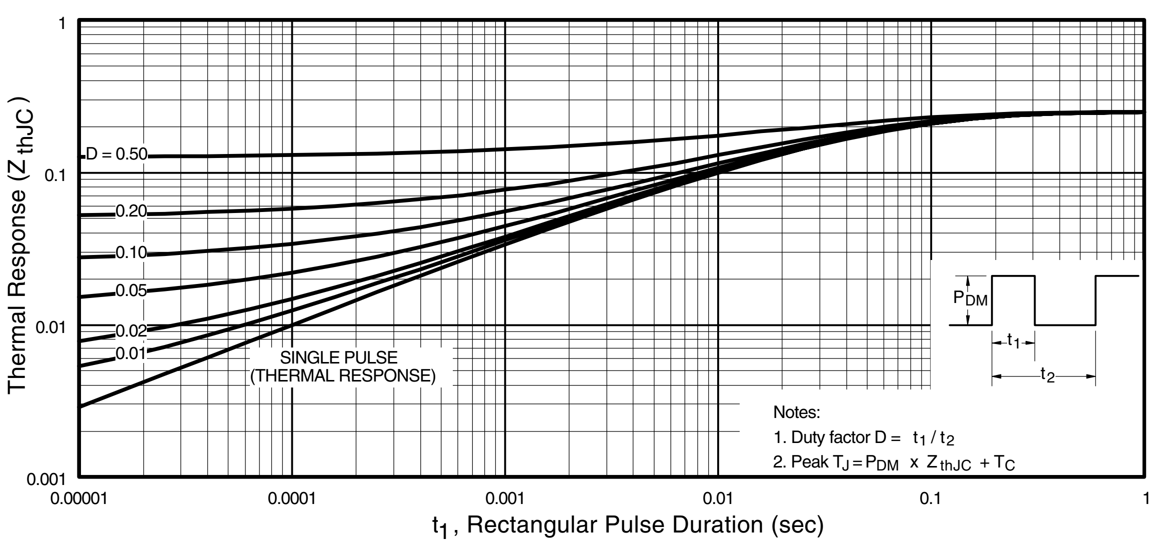


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

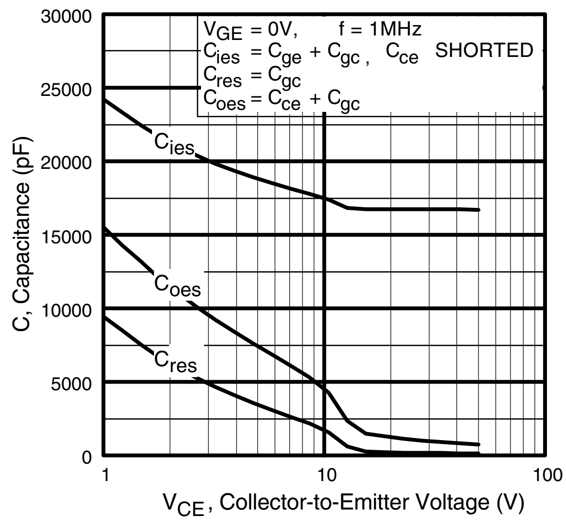


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

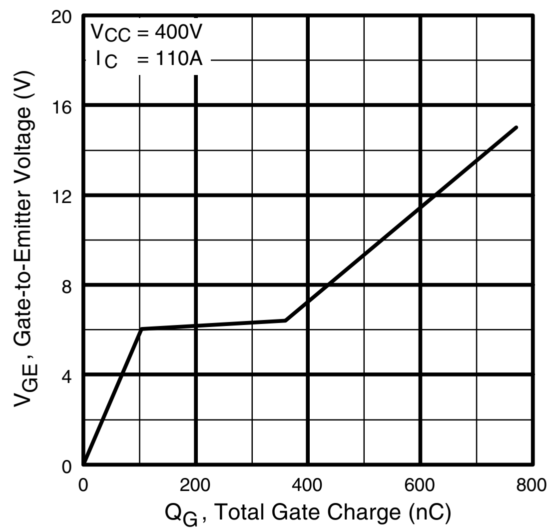


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

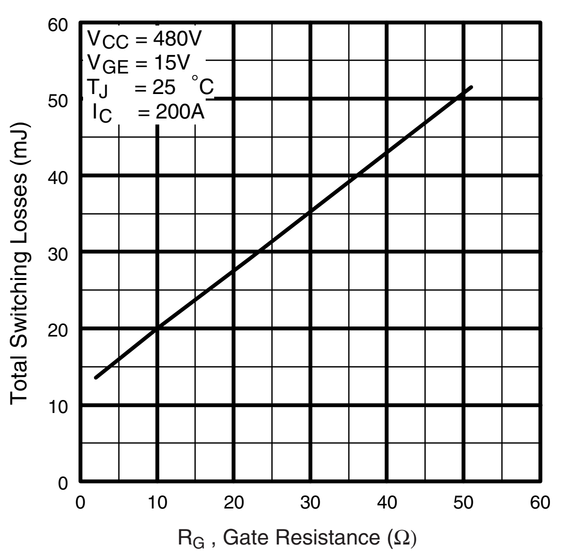


Fig. 9 - Typical Switching Losses vs. Gate Resistance

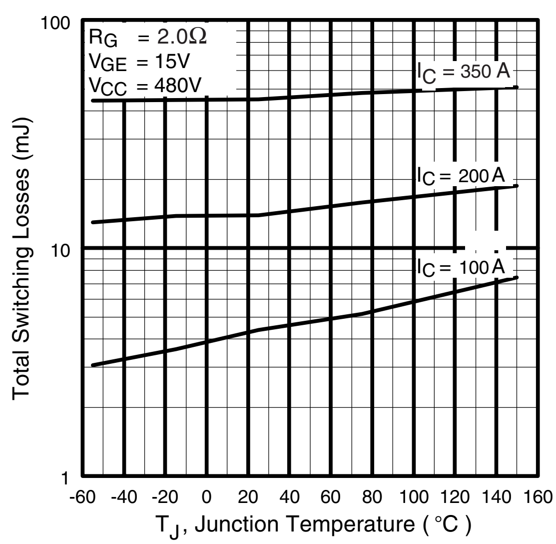


Fig. 10 - Typical Switching Losses vs. Junction Temperature

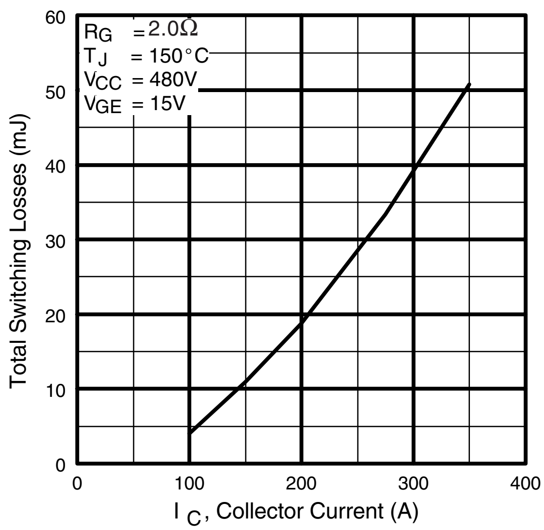


Fig. 11 - Typical Switching Losses vs. Collector Current

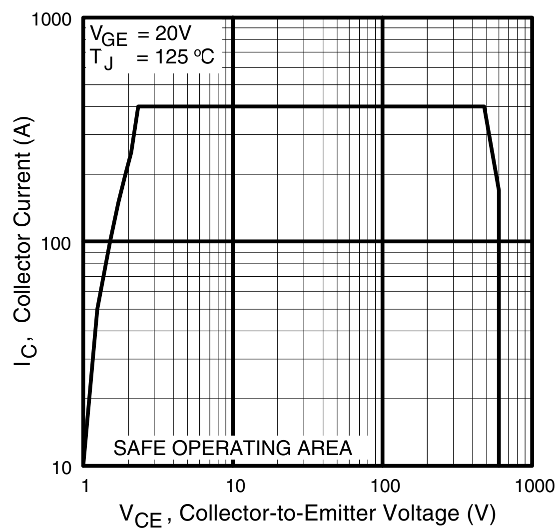


Fig. 12 - Turn-Off SOA

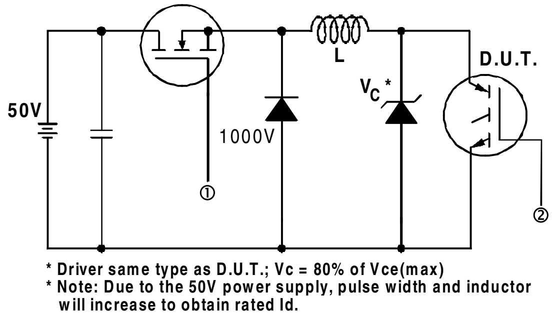


Fig. 13a - Clamped Inductive Load Test Circuit

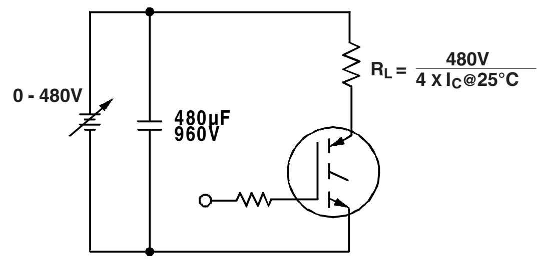


Fig. 13b - Pulsed Collector Current Test Circuit

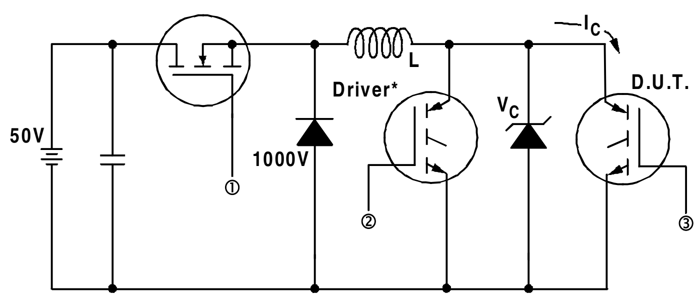


Fig. 14a - Switching Loss Test Circuit

* Driver same type as D.U.T., VC = 480V

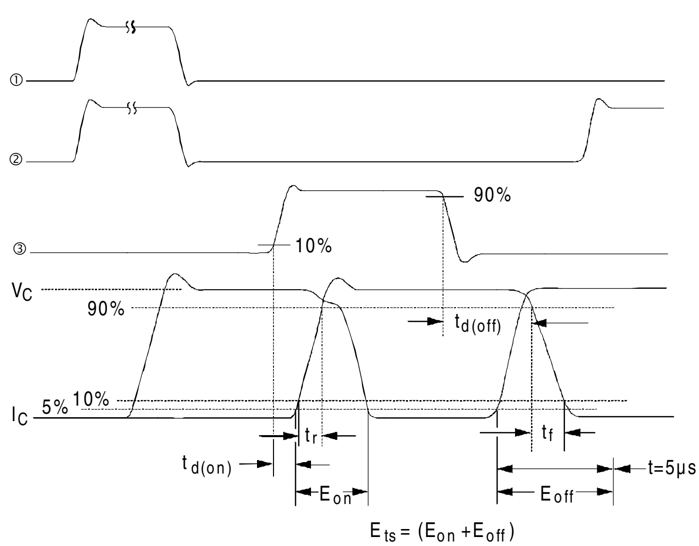


Fig. 14b - Switching Loss Waveforms

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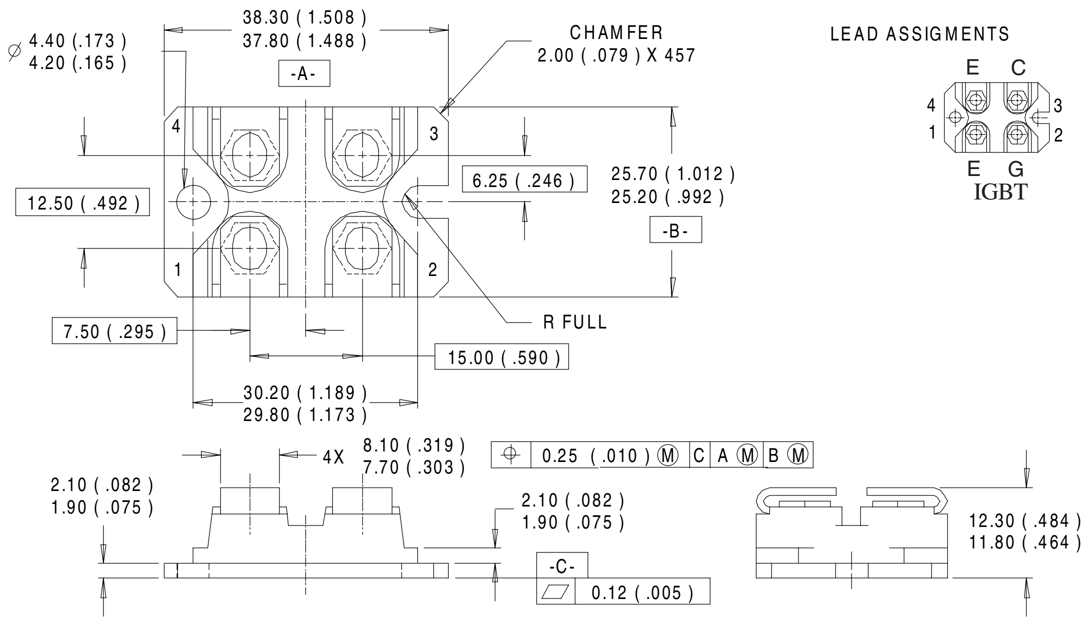
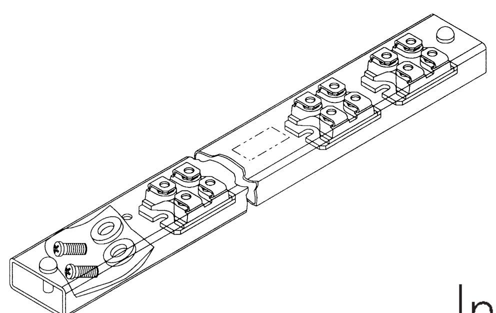
SOT-227 Package Details

Dimensions are shown in millimeters (inches)



Tube

QUANTITIES PER TUBE IS 10
M4 SREW AND WASHER INCLUDED



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Data and specifications subject to change without notice. 4/00

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